

100-Pin TQFP  
Commercial Temp  
Industrial Temp

**1M x 18, 512K x 32, 512K x 36**  
**16Mb Sync Burst SRAMs**

7 ns 11 ns  
3.3 V  $V_{DD}$   
2.5 V or 3.3 V I/O

## Features

- Flow Through mode operation; Pin 14 = No Connect
- 3.3 V +10%/−5% core power supply
- 2.5 V or 3.3 V I/O supply
- $\overline{LBO}$  pin for Linear or Interleaved Burst mode
- Internal input resistors on mode pins allow floating mode pins
- Byte Write ( $\overline{BW}$ ) and/or Global Write ( $\overline{GW}$ ) operation
- Internal self-timed write cycle
- Automatic power-down for portable applications
- JEDEC-standard 100-lead TQFP package

		-7	-7.5	-8	-8.5	-10	-11	Unit
Flow	$t_{KQ}$	7.0	7.5	8	8.5	10	11	ns
Through	$t_{Cycle}$	8.5	10	10	10	10	15	ns
2-1-1-1	Curr (x18)	205	185	185	185	185	140	mA
	Curr (x32)	240	210	210	210	210	160	mA
	Curr (x36)	240	210	210	210	210	160	mA

## Functional Description

### Applications

The GS8150F18/32/36T is a 18,874,368-bit (16,777,216-bit for x32 version) high performance synchronous SRAM with a 2-bit burst address counter. Although of a type originally developed for Level 2 Cache applications supporting high performance CPUs, the device now finds application in synchronous SRAM applications, ranging from DSP main store to networking chip set support.

### Controls

Addresses, data I/Os, chip enables ( $\overline{E1}$ ,  $\overline{E2}$ ,  $\overline{E3}$ ), address burst control inputs ( $\overline{ADSP}$ ,  $\overline{ADSC}$ ,  $\overline{ADV}$ ), and write control inputs ( $\overline{Bx}$ ,  $\overline{BW}$ ,  $\overline{GW}$ ) are synchronous and are controlled by a positive-edge-triggered clock input (CK). Output enable ( $\overline{G}$ ) and power down control (ZZ) are asynchronous inputs. Burst cycles can be initiated with either  $\overline{ADSP}$  or  $\overline{ADSC}$  inputs. In Burst mode, subsequent burst addresses are generated internally and are controlled by  $\overline{ADV}$ . The burst address counter may be configured to count in either linear or interleave order with the Linear Burst Order ( $\overline{LBO}$ ) input. The Burst function need not be used. New addresses can be loaded on every cycle with no degradation of chip performance.

### Designing For Compatibility

The JEDEC standard for Burst RAMS calls for a  $\overline{FT}$  mode pin option on Pin 14. Board sites for flow through Burst RAMS

should be designed with  $V_{SS}$  connected to the  $\overline{FT}$  pin location to ensure the broadest access to multiple vendor sources. Boards designed with  $\overline{FT}$  pin pads tied low may be stuffed with GSI's pipeline/flow through-configurable Burst RAMs or any vendor's flow through or configurable Burst SRAM. Boards designed with the  $\overline{FT}$  pin location tied high or floating must employ a non-configurable flow through Burst RAM, like this RAM, to achieve flow through functionality.

### Byte Write and Global Write

Byte write operation is performed by using Byte Write enable ( $\overline{BW}$ ) input combined with one or more individual byte write signals ( $\overline{Bx}$ ). In addition, Global Write ( $\overline{GW}$ ) is available for writing all bytes at one time, regardless of the Byte Write control inputs.

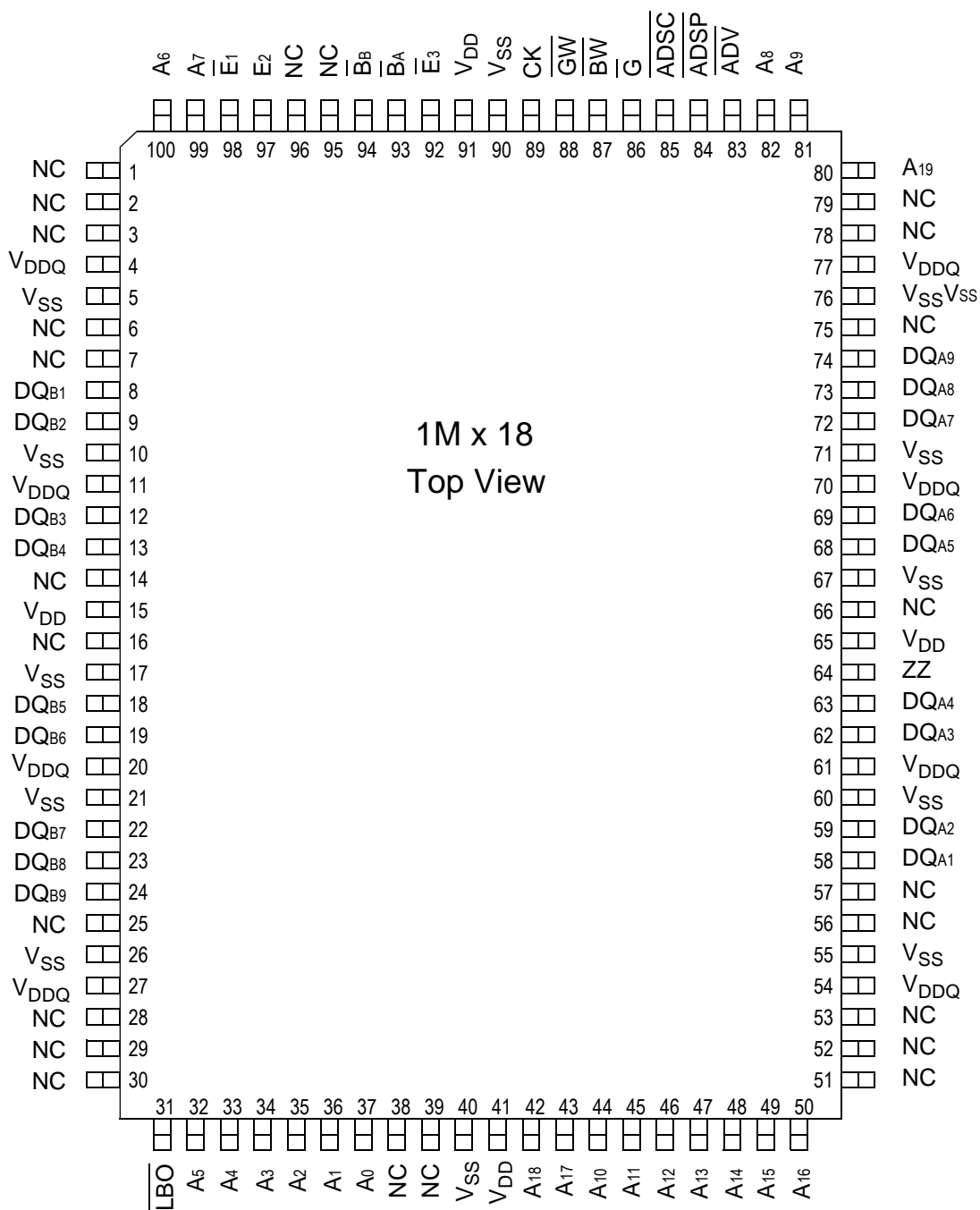
### Sleep Mode

Low power (Sleep mode) is attained through the assertion (High) of the ZZ signal, or by stopping the clock (CK). Memory data is retained during Sleep mode.

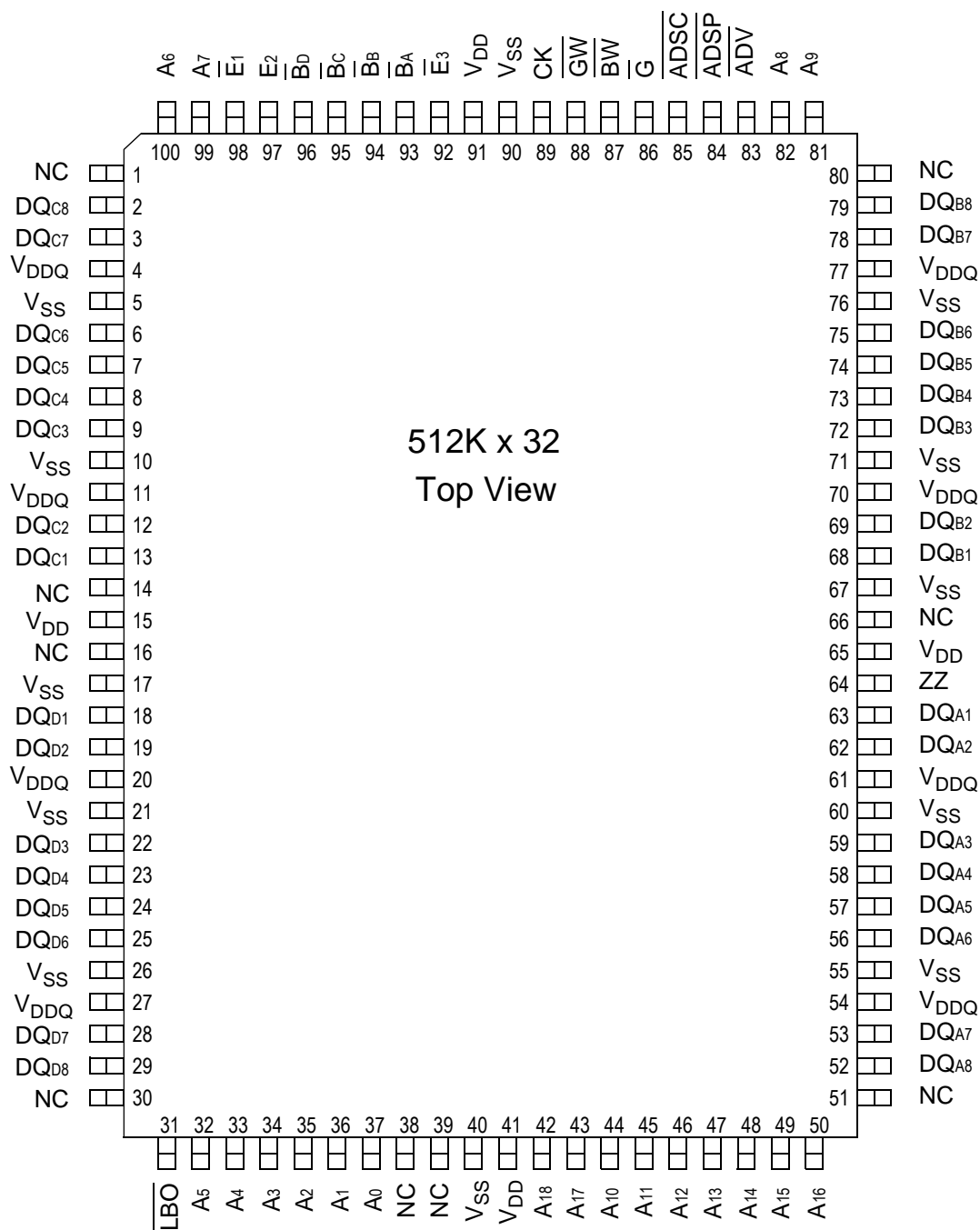
### Core and Interface Voltages

The GS8150F18/32/36T operates on a 3.3 V power supply. All input are 3.3 V- and 2.5 V-compatible. Separate output power ( $V_{DDQ}$ ) pins are used to decouple output noise from the internal circuits and are 3.3 V- and 2.5 V-compatible.

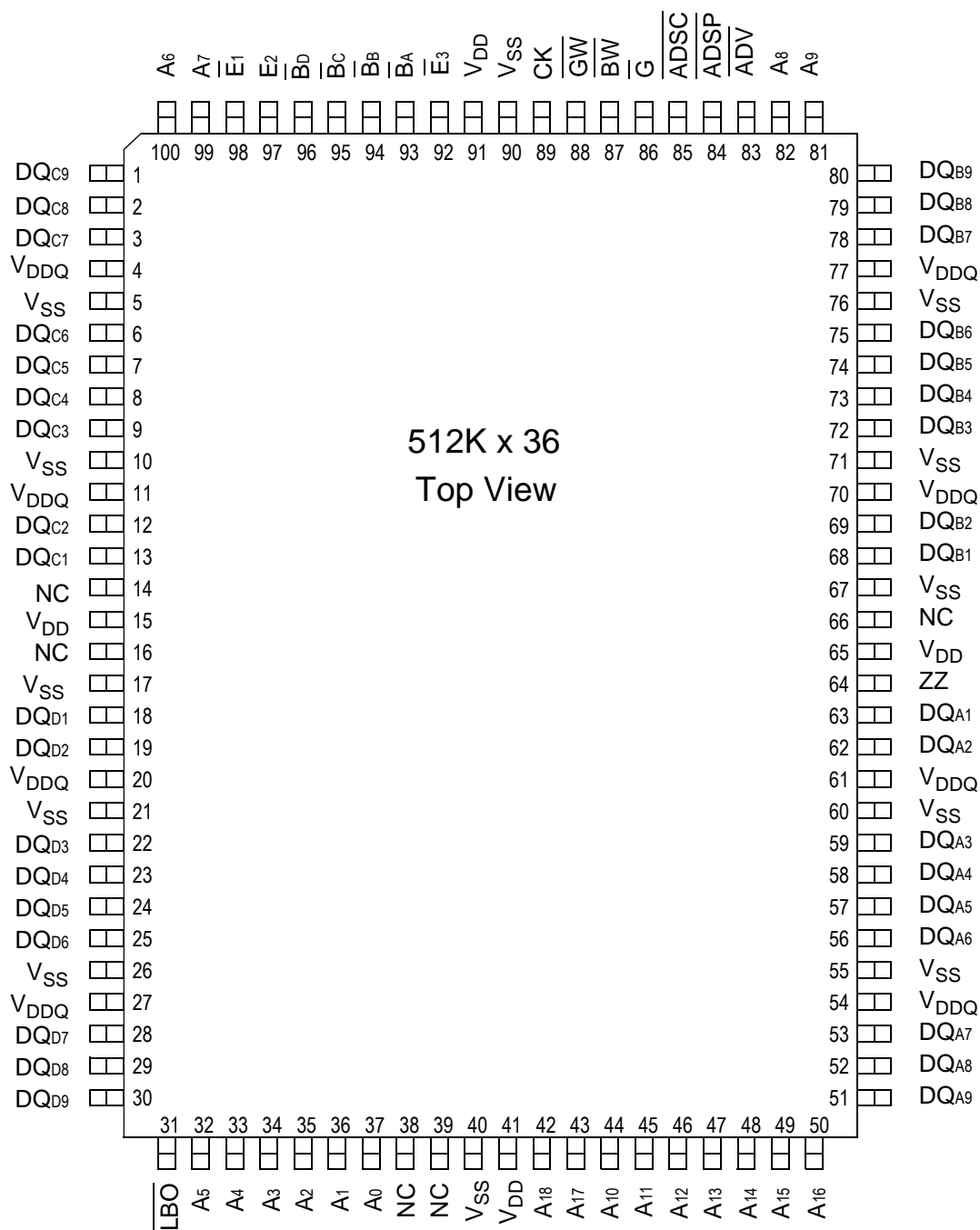
GS8150F18 100-Pin TQFP Pinout



GS8150F32 100-Pin TQFP Pinout



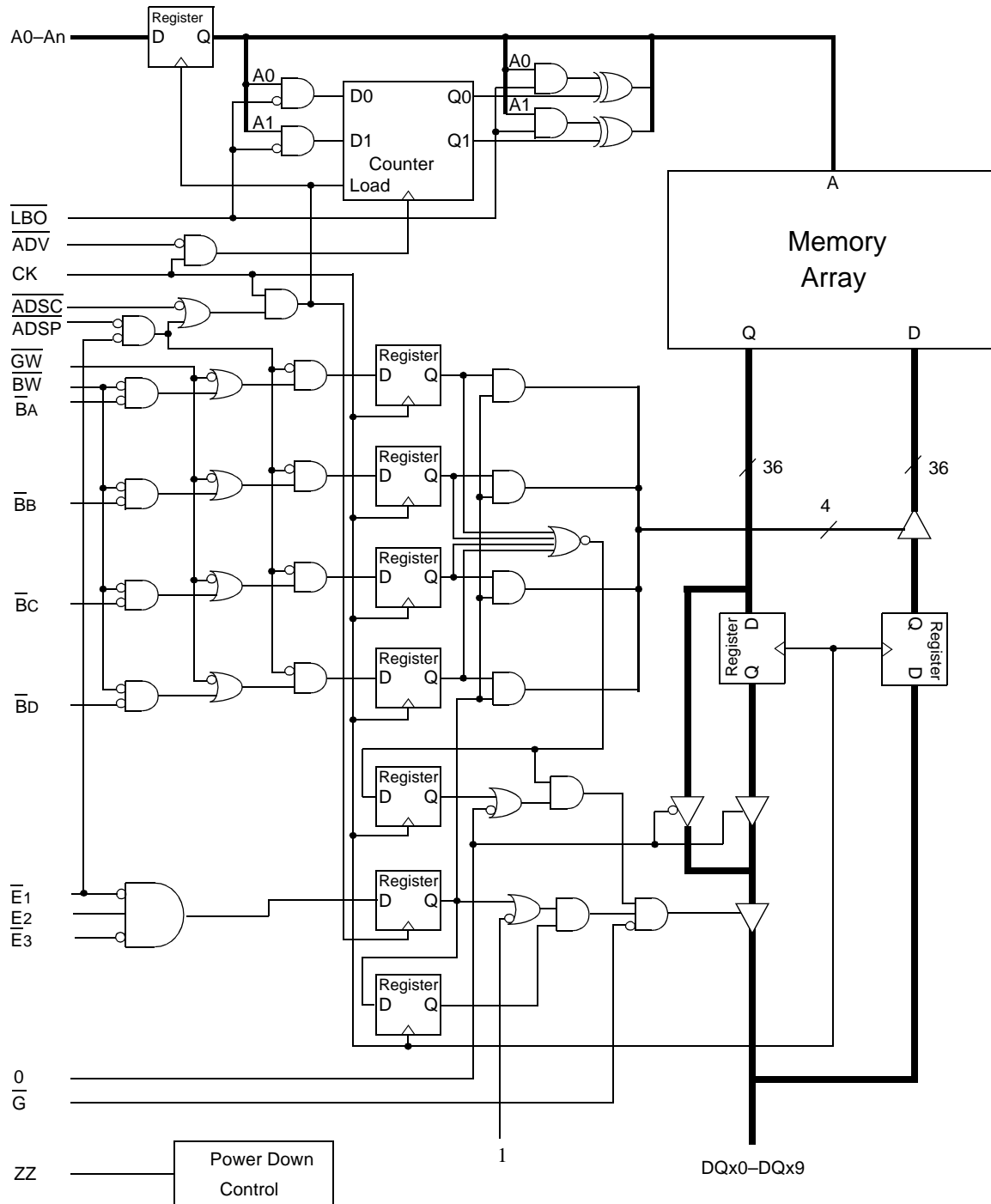
GS8150F36 100-Pin TQFP Pinout



### TQFP Pin Description

Pin Location	Symbol	Type	Description
37, 36	A <sub>0</sub> , A <sub>1</sub>	I	Address field LSBs and Address Counter preset Inputs
35, 34, 33, 32, 100, 99, 82, 81, 44, 45, 46, 47, 48, 49, 50, 43, 42,	A <sub>2</sub> –A <sub>18</sub>	I	Address Inputs
80	A <sub>19</sub>	I	Address Inputs (x18 versions)
63, 62, 59, 58, 57, 53, 52 68, 69, 72, 73, 74, 75, 78, 79 13, 12, 9, 8, 7, 6, 3, 2 18, 19, 22, 23, 24, 25, 28, 29	DQA <sub>1</sub> –DQA <sub>8</sub> DQB <sub>1</sub> –DQB <sub>8</sub> DQC <sub>1</sub> –DQC <sub>8</sub> DQD <sub>1</sub> –DQD <sub>8</sub>	I/O	Data Input and Output pins (x32, x36 Version)
51, 80, 1, 30	DQA <sub>9</sub> , DQB <sub>9</sub> , DQC <sub>9</sub> , DQD <sub>9</sub>	I/O	Data Input and Output pins (x36 Version)
58, 59, 62, 63, 68, 69, 72, 73, 74 8, 9, 12, 13, 18, 19, 22, 23, 24	DQA <sub>1</sub> –DQA <sub>9</sub> DQB <sub>1</sub> –DQB <sub>9</sub>	I/O	Data Input and Output pins (x18 Version)
51, 52, 53, 56, 57 75, 78, 79, 1, 2, 3, 6, 7, 25, 28, 29, 30	NC	—	No Connect (x18 Version)
87	BW	I	Byte Write Writes all enabled bytes; active low
93, 94	BA, BB	I	Byte Write Enable for DQA, DQB Data I/Os; active low
95, 96	$\overline{B}C$ , $\overline{B}D$	I	Byte Write Enable for DQC, DQD Data I/Os; active low (x32, x36 Version)
95, 96	NC	—	No Connect (x18 Version)
89	CK	I	Clock Input Signal; active high
88	$\overline{G}W$	I	Global Write Enable Writes all bytes; active low
98, 92	E <sub>1</sub> , E <sub>3</sub>	I	Chip Enable; active low
97	E <sub>2</sub>	I	Chip Enable; active high
86	$\overline{G}$	I	Output Enable; active low
83	$\overline{A}DV$	I	Burst address counter advance enable; active low
84, 85	ADSP, ADSC	I	Address Strobe (Processor, Cache Controller); active low
64	$\overline{Z}Z$	I	Sleep Mode control; active high
31	LBO	I	Linear Burst Order mode; active low
15, 41, 65, 91	V <sub>DD</sub>	I	Core power supply
5,10,17, 21, 26, 40, 55, 60, 67, 71, 76, 90	V <sub>SS</sub>	I	I/O and Core Ground
4, 11, 20, 27, 54, 61, 70, 77	V <sub>DDQ</sub>	I	Output driver power supply
14, 16, 38, 39, 66	NC	—	No Connect

### GS8150F18/32/36 Block Diagram



Note: Only x36 version shown for simplicity.

### Mode Pin Functions

Mode Name	Pin Name	State	Function
Burst Order Control	$\overline{\text{LBO}}$	L	Linear Burst
		H	Interleaved Burst
Power Down Control	ZZ	L or NC	Active
		H	Standby, $I_{DD} = I_{SB}$

Note:

There is a pull-down device on the ZZ pin, so this input pin can be unconnected and the chip will operate in the default states as specified in the above tables.

### Burst Counter Sequences

#### Linear Burst Sequence

	A[1:0]	A[1:0]	A[1:0]	A[1:0]
1st address	00	01	10	11
2nd address	01	10	11	00
3rd address	10	11	00	01
4th address	11	00	01	10

Note: The burst counter wraps to initial state on the 5th clock.

#### Interleaved Burst Sequence

	A[1:0]	A[1:0]	A[1:0]	A[1:0]
1st address	00	01	10	11
2nd address	01	00	11	10
3rd address	10	11	00	01
4th address	11	10	01	00

Note: The burst counter wraps to initial state on the 5th clock.

BPR 1999.05.18

### Byte Write Truth Table

Function	$\overline{\text{GW}}$	$\overline{\text{BW}}$	$\overline{\text{BA}}$	$\overline{\text{BB}}$	$\overline{\text{BC}}$	$\overline{\text{BD}}$	Notes
Read	H	H	X	X	X	X	1
Read	H	L	H	H	H	H	1
Write byte a	H	L	L	H	H	H	2, 3
Write byte b	H	L	H	L	H	H	2, 3
Write byte c	H	L	H	H	L	H	2, 3, 4
Write byte d	H	L	H	H	H	L	2, 3, 4
Write all bytes	H	L	L	L	L	L	2, 3, 4
Write all bytes	L	X	X	X	X	X	

Notes:

- All byte outputs are active in read cycles regardless of the state of Byte Write Enable inputs.
- Byte Write Enable inputs BA, BB, BC, and/or BD may be used in any combination with BW to write single or multiple bytes.
- All byte I/Os remain High-Z during all write operations regardless of the state of Byte Write Enable inputs.
- Bytes C and D are only available on the x32 and x36 versions.

### Synchronous Truth Table

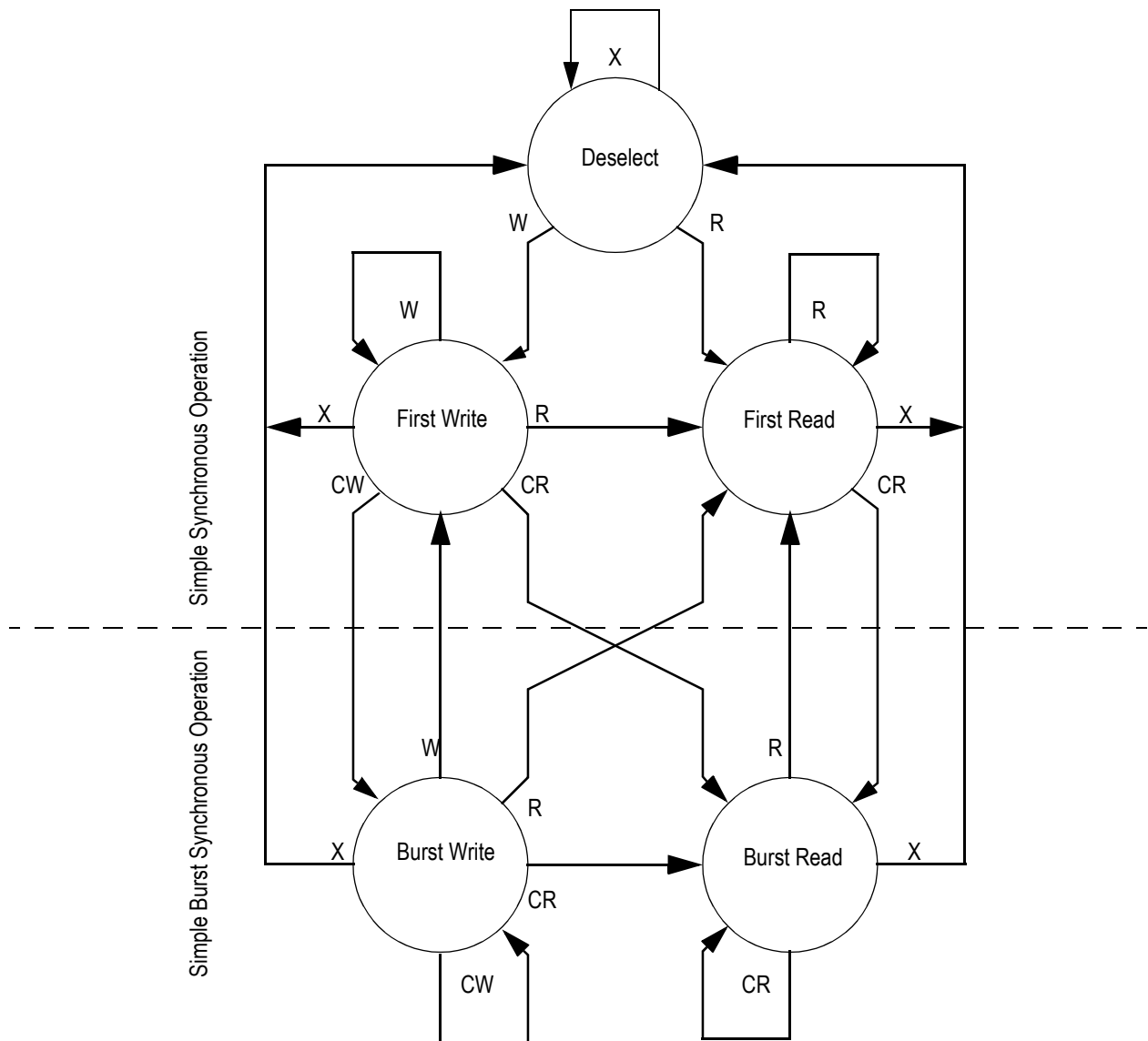
Operation	Address Used	State Diagram Key <sup>5</sup>	$\bar{E}_1$	$E^2$	$\overline{ADSP}$	$\overline{ADSC}$	$\overline{ADV}$	$\bar{W}^3$	DQ <sup>4</sup>
<b>Deselect Cycle, Power Down</b>	<b>None</b>	<b>X</b>	<b>H</b>	<b>X</b>	<b>X</b>	<b>L</b>	<b>X</b>	<b>X</b>	<b>High-Z</b>
Deselect Cycle, Power Down	None	X	L	F	L	X	X	X	High-Z
<b>Deselect Cycle, Power Down</b>	<b>None</b>	<b>X</b>	<b>L</b>	<b>F</b>	<b>H</b>	<b>L</b>	<b>X</b>	<b>X</b>	<b>High-Z</b>
Read Cycle, Begin Burst	External	R	L	T	L	X	X	X	Q
<b>Read Cycle, Begin Burst</b>	<b>External</b>	<b>R</b>	<b>L</b>	<b>T</b>	<b>H</b>	<b>L</b>	<b>X</b>	<b>F</b>	<b>Q</b>
<b>Write Cycle, Begin Burst</b>	<b>External</b>	<b>W</b>	<b>L</b>	<b>T</b>	<b>H</b>	<b>L</b>	<b>X</b>	<b>T</b>	<b>D</b>
<i>Read Cycle, Continue Burst</i>	<i>Next</i>	<i>CR</i>	<i>X</i>	<i>X</i>	<i>H</i>	<i>H</i>	<i>L</i>	<i>F</i>	<i>Q</i>
Read Cycle, Continue Burst	Next	CR	H	X	X	H	L	F	Q
<i>Write Cycle, Continue Burst</i>	<i>Next</i>	<i>CW</i>	<i>X</i>	<i>X</i>	<i>H</i>	<i>H</i>	<i>L</i>	<i>T</i>	<i>D</i>
Write Cycle, Continue Burst	Next	CW	H	X	X	H	L	T	D
Read Cycle, Suspend Burst	Current		X	X	H	H	H	F	Q
Read Cycle, Suspend Burst	Current		H	X	X	H	H	F	Q
Write Cycle, Suspend Burst	Current		X	X	H	H	H	T	D
Write Cycle, Suspend Burst	Current		H	X	X	H	H	T	D

Notes:

1. X = Don't Care, H = High, L = Low
2. E = T (True) if  $E_2 = 1$ ; E = F (False) if  $E_2 = 0$
3.  $\bar{W} = T$  (True) and F (False) is defined in the Byte Write Truth Table preceding
4.  $\bar{G}$  is an asynchronous input.  $\bar{G}$  can be driven high at any time to disable active output drivers.  $\bar{G}$  low can only enable active drivers (shown as Q in the Truth Table above).
5. All input combinations shown above are tested and supported. Input combinations shown in gray boxes need not be used to accomplish basic synchronous or synchronous burst operations and may be avoided for simplicity.
6. Tying  $\overline{ADSP}$  high and  $\overline{ADSC}$  low allows simple non-burst synchronous operations. See **BOLD** items above.
7. Tying  $\overline{ADSP}$  high and  $\overline{ADV}$  low while using  $\overline{ADSC}$  to load new addresses allows simple burst operations. See *ITALIC* items above.



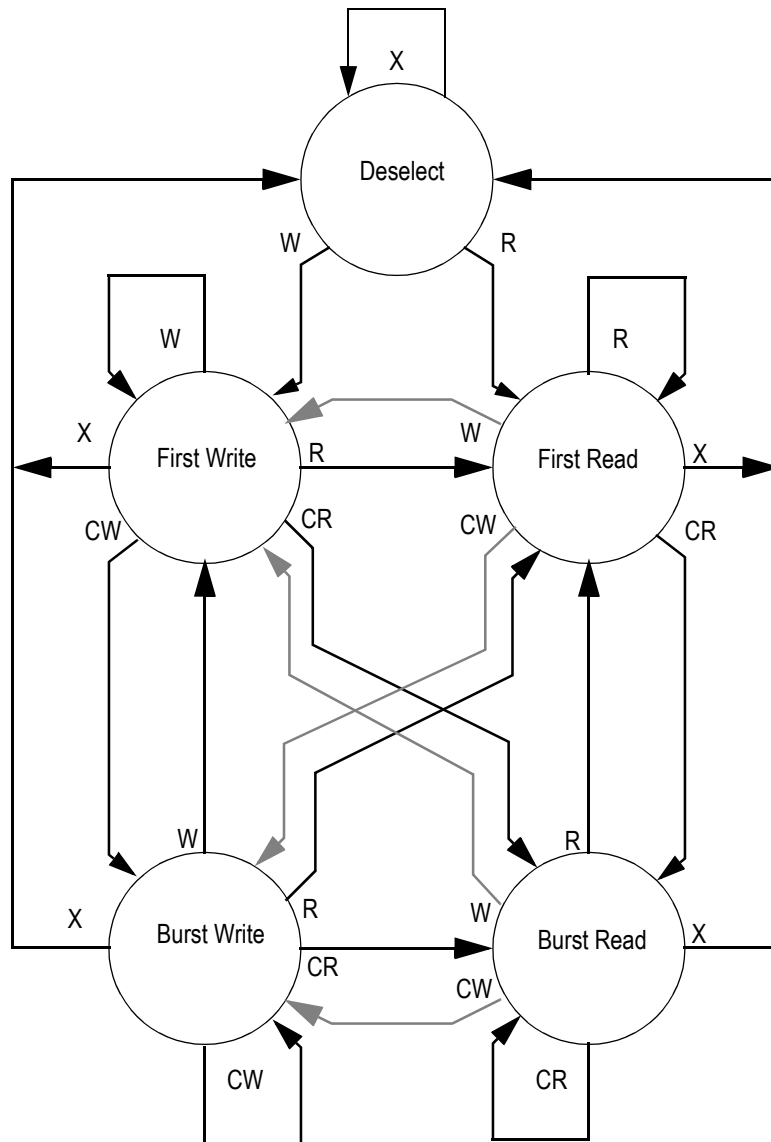
## Simplified State Diagram



Notes:

1. The diagram shows only supported (tested) synchronous state transitions. The diagram presumes  $\overline{G}$  is tied low.
2. The upper portion of the diagram assumes active use of only the Enable ( $\overline{E1}$ ,  $\overline{E2}$ , and  $\overline{E3}$ ) and Write ( $\overline{BA}$ ,  $\overline{BB}$ ,  $\overline{BC}$ ,  $\overline{BD}$ ,  $\overline{BW}$ , and  $\overline{GW}$ ) control inputs and that  $\overline{ADSP}$  is tied high and  $\overline{ADSC}$  is tied low.
3. The upper and lower portions of the diagram together assume active use of only the Enable, Write, and  $\overline{ADSC}$  control inputs and assumes  $\overline{ADSP}$  is tied high and  $\overline{ADV}$  is tied low.

## Simplified State Diagram with $\overline{G}$



**Notes:**

1. The diagram shows supported (tested) synchronous state transitions plus supported transitions that depend upon the use of  $\overline{G}$ .
2. Use of Dummy Reads (Read Cycles with  $\overline{G}$  High) may be used to make the transition from read cycles to write cycles without passing through a Deselect cycle. Dummy Read cycles increment the address counter just like normal read cycles.
3. Transitions shown in grey tone assume  $\overline{G}$  has been pulsed high long enough to turn the RAM's drivers off and for incoming data to meet Data Input Set Up Time.

### Absolute Maximum Ratings

(All voltages reference to  $V_{SS}$ )

Symbol	Description	Value	Unit
$V_{DD}$	Voltage on $V_{DD}$ Pins	0.5 to 4.6	V
$V_{DDQ}$	Voltage in $V_{DDQ}$ Pins	0.5 to $V_{DD}$	V
$V_{CK}$	Voltage on Clock Input Pin	0.5 to 6	V
$V_{I/O}$	Voltage on I/O Pins	0.5 to $V_{DDQ} + 0.5$ ( $\leq 4.6$ V max.)	V
$V_{IN}$	Voltage on Other Input Pins	0.5 to $V_{DD} + 0.5$ ( $\leq 4.6$ V max.)	V
$I_{IN}$	Input Current on Any Pin	+/- 20	mA
$I_{OUT}$	Output Current on Any I/O Pin	+/- 20	mA
$P_D$	Package Power Dissipation	1.5	W
$T_{STG}$	Storage Temperature	55 to 125	$^{\circ}C$
$T_{BIAS}$	Temperature Under Bias	55 to 125	$^{\circ}C$

**Note:**

Permanent damage to the device may occur if the Absolute Maximum Ratings are exceeded. Operation should be restricted to Recommended Operating Conditions. Exposure to conditions exceeding the Absolute Maximum Ratings, for an extended period of time, may affect reliability of this component.

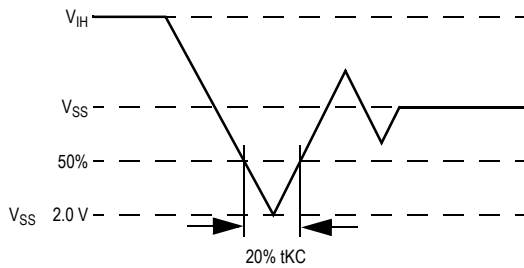
### Recommended Operating Conditions

Parameter	Symbol	Min.	Typ.	Max.	Unit	Notes
Supply Voltage	$V_{DD}$	3.135	3.3	3.6	V	
I/O Supply Voltage	$V_{DDQ}$	2.375	2.5	$V_{DD}$	V	1
Input High Voltage	$V_{IH}$	1.7		$V_{DD} + 0.3$	V	2
Input Low Voltage	$V_{IL}$	0.3		0.8	V	2
Ambient Temperature (Commercial Range Versions)	$T_A$	0	25	70	$^{\circ}C$	3
Ambient Temperature (Industrial Range Versions)	$T_A$	40	25	85	$^{\circ}C$	3

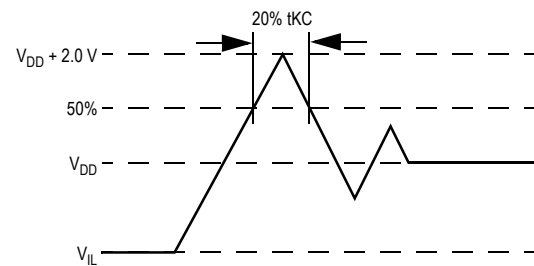
**Notes:**

- Unless otherwise noted, all performance specifications quoted are evaluated for worst case at both  $2.75\text{ V} \leq V_{DDQ} \leq 2.375\text{ V}$  (i.e., 2.5 V I/O) and  $3.6\text{ V} \leq V_{DDQ} \leq 3.135\text{ V}$  (i.e., 3.3 V I/O), and quoted at whichever condition is worst case.
- This device features input buffers compatible with both 3.3 V and 2.5 V I/O drivers.
- Most speed grades and configurations of this device are offered in both Commercial and Industrial Temperature ranges. The part number of Industrial Temperature Range versions end the character I. Unless otherwise noted, all performance specifications quoted are evaluated for worst case in the temperature range marked on the device.
- Input Under/overshoot voltage must be  $-2\text{ V} > V_i < V_{DD} + 2\text{ V}$  with a pulse width not to exceed 20% tKC.

### Undershoot Measurement and Timing



### Overshoot Measurement and Timing



### Capacitance

( $T_A = 25^\circ\text{C}$ ,  $f = 1\text{ MHz}$ ,  $V_{DD} = 3.3\text{ V}$ )

Parameter	Symbol	Test conditions	Typ.	Max.	Unit
Input Capacitance	$C_{IN}$	$V_{IN} = 0\text{ V}$	4	5	pF
Input/Output Capacitance	$C_{I/O}$	$V_{OUT} = 0\text{ V}$	6 (x36) 12 (x18)	7 (x36) 12 (x18)	pF

Note: These parameters are sample tested.

### Package Thermal Characteristics

Rating	Layer Board	Symbol	Max	Unit	Notes
Junction to Ambient (at 200 lfm)	single	$R_{\theta JA}$	40	$^\circ\text{C/W}$	1,2
Junction to Ambient (at 200 lfm)	four	$R_{\theta JA}$	24	$^\circ\text{C/W}$	1,2
Junction to Case (TOP)		$R_{\theta JC}$	9	$^\circ\text{C/W}$	3

Notes:

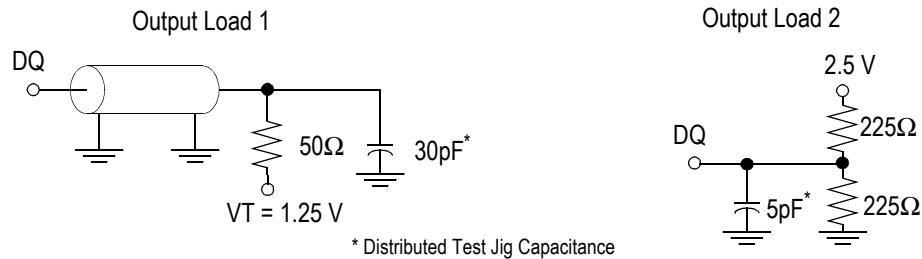
- Junction temperature is a function of SRAM power dissipation, package thermal resistance, mounting board temperature, ambient. Temperature air flow, board density, and PCB thermal resistance.
- SCMI G-38-87
- Average thermal resistance between die and top surface, MIL SPEC-883, Method 1012.1

### AC Test Conditions

Parameter	Conditions
Input high level	2.3 V
Input low level	0.2 V
Input slew rate	1 V/ns
Input reference level	1.25 V
Output reference level	1.25 V
Output load	<b>Fig. 1 &amp; 2</b>

Notes:

1. Include scope and jig capacitance.
2. Test conditions as specified with output loading as shown in **Fig. 1** unless otherwise noted.
3. Output Load 2 for  $t_{LZ}$ ,  $t_{HZ}$ ,  $t_{OLZ}$  and  $t_{OHZ}$
4. Device is deselected as defined by the Truth Table.



### DC Electrical Characteristics

Parameter	Symbol	Test Conditions	Min	Max
Input Leakage Current (except mode pins)	$I_{IL}$	$V_{IN} = 0 \text{ to } V_{DD}$	1 $\mu\text{A}$	1 $\mu\text{A}$
ZZ Input Current	$I_{INZZ}$	$V_{DD} \geq V_{IN} \geq V_{IH}$ $0 \text{ V} \leq V_{IN} \leq V_{IH}$	1 $\mu\text{A}$ 1 $\mu\text{A}$	1 $\mu\text{A}$ 300 $\mu\text{A}$
Mode Pin Input Current	$I_{INM}$	$V_{DD} \geq V_{IN} \geq V_{IL}$ $0 \text{ V} \leq V_{IN} \leq V_{IL}$	300 $\mu\text{A}$ 1 $\mu\text{A}$	1 $\mu\text{A}$ 1 $\mu\text{A}$
Output Leakage Current	$I_{OL}$	Output Disable, $V_{OUT} = 0 \text{ to } V_{DD}$	1 $\mu\text{A}$	1 $\mu\text{A}$
Output High Voltage	$V_{OH}$	$I_{OH} = 4 \text{ mA}$ , $V_{DDQ} = 2.375 \text{ V}$	1.7 V	
Output High Voltage	$V_{OH}$	$I_{OH} = 4 \text{ mA}$ , $V_{DDQ} = 3.135 \text{ V}$	2.4 V	
Output Low Voltage	$V_{OL}$	$I_{OL} = 4 \text{ mA}$		0.4 V

### Operating Currents

Parameter	Test Conditions	Mode	Symbol	-7		-7.5		-8		-8.5		-10		-11		Unit
				0 to 70°C	-40 to 85°C	0 to 70°C	-40 to 85°C	0 to 70°C	-40 to 85°C	0 to 70°C	-40 to 85°C	0 to 70°C	-40 to 85°C	0 to 70°C	-40 to 85°C	
Operating Current	Device Selected; All other inputs $\geq V_{IH}$ or $\leq V_{IL}$ Output open	(x36)	$I_{DD}$	199	209	177	187	177	187	177	187	177	187	134	144	mA
			$I_{DDQ}$	39	49	33	43	33	43	33	43	33	43	22	32	
Standby Current	$ZZ \geq V_{DD} - 0.2 V$	—	$I_{DD}$	186	196	166	176	166	176	166	176	166	176	127	137	mA
					$I_{DDQ}$	19	29	17	27	17	27	17	27	17	27	
Deselect Current	Device Deselected; All other inputs $\geq V_{IH}$ or $\leq V_{IL}$	—	$I_{SB}$	10	20	10	20	10	20	10	20	10	20	10	20	mA
					$I_{DD}$	60	65	50	55	50	55	50	55	50	55	

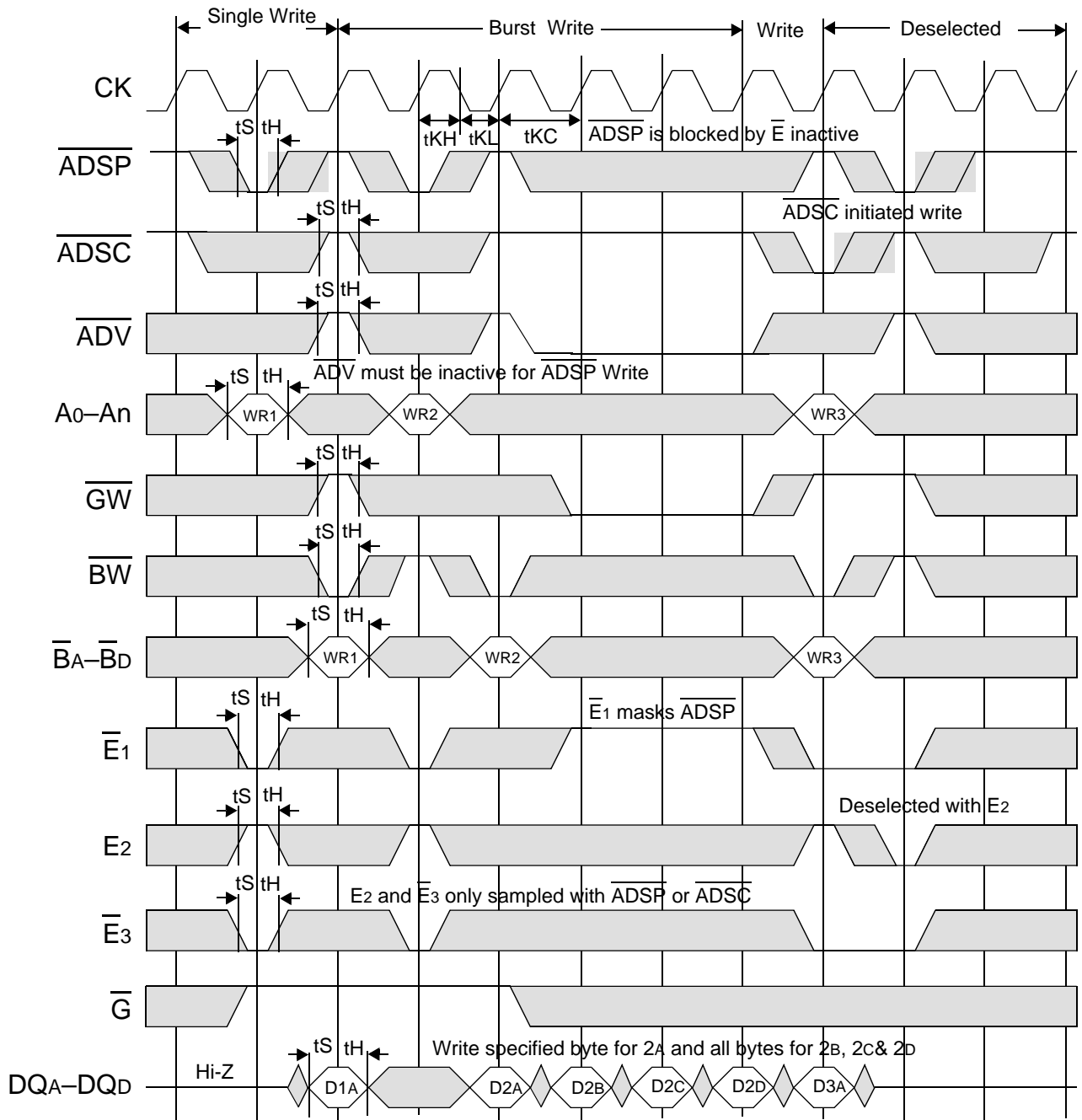
## AC Electrical Characteristics

	Parameter	Symbol	-7 ns		-7.5 ns		-8 ns		-8.5 ns		-10 ns		-11 ns		Unit
			Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
Flow Through	Clock Cycle Time	tKC	8.5	—	10.0		10.0		10.0		10.0		15.0		ns
	Clock to Output Valid	tKQ		7		7.5		8.0		8.5		10.0		11.0	ns
	Clock to Output Invalid	tKQX	3.0		3.0		3.0		3.0		3.0		3.0		ns
	Clock to Output in Low-Z	tLZ <sup>1</sup>	3.0		3.0		3.0		3.0		3.0		3.0		ns
	Clock HIGH Time	tKH	1.3		1.3		1.3		1.3		1.5		1.7		ns
	Clock LOW Time	tKL	1.5		1.5		1.5		1.5		1.7		2		ns
	Clock to Output in High-Z	tHZ <sup>1</sup>	1.5	2.5	1.5	3.0	1.5	3.2	1.5	3.5	1.5	3.8	1.5	4.0	ns
	$\bar{G}$ to Output Valid	tOE		2.5		3.2		3.2		3.5		3.8		4.0	ns
	$\bar{G}$ to output in Low-Z	tOLZ <sup>1</sup>	0		0		0		0		0		0		ns
	$\bar{G}$ to output in High-Z	tOHZ <sup>1</sup>		2.5		3.0		3.2		3.5		3.8		4.0	ns
	Setup time	tS	1.5		1.5		1.5		1.5		1.5		1.5		ns
	Hold time	tH	0.5		0.5		0.5		0.5		0.5		0.5		ns
	ZZ setup time	tZZS <sup>2</sup>	5		5		5		5		5		5		ns
	ZZ hold time	tZZH <sup>2</sup>	1		1		1		1		1		1		ns
ZZ recovery	tZZR	100		100		100		100		100		100		ns	

Notes:

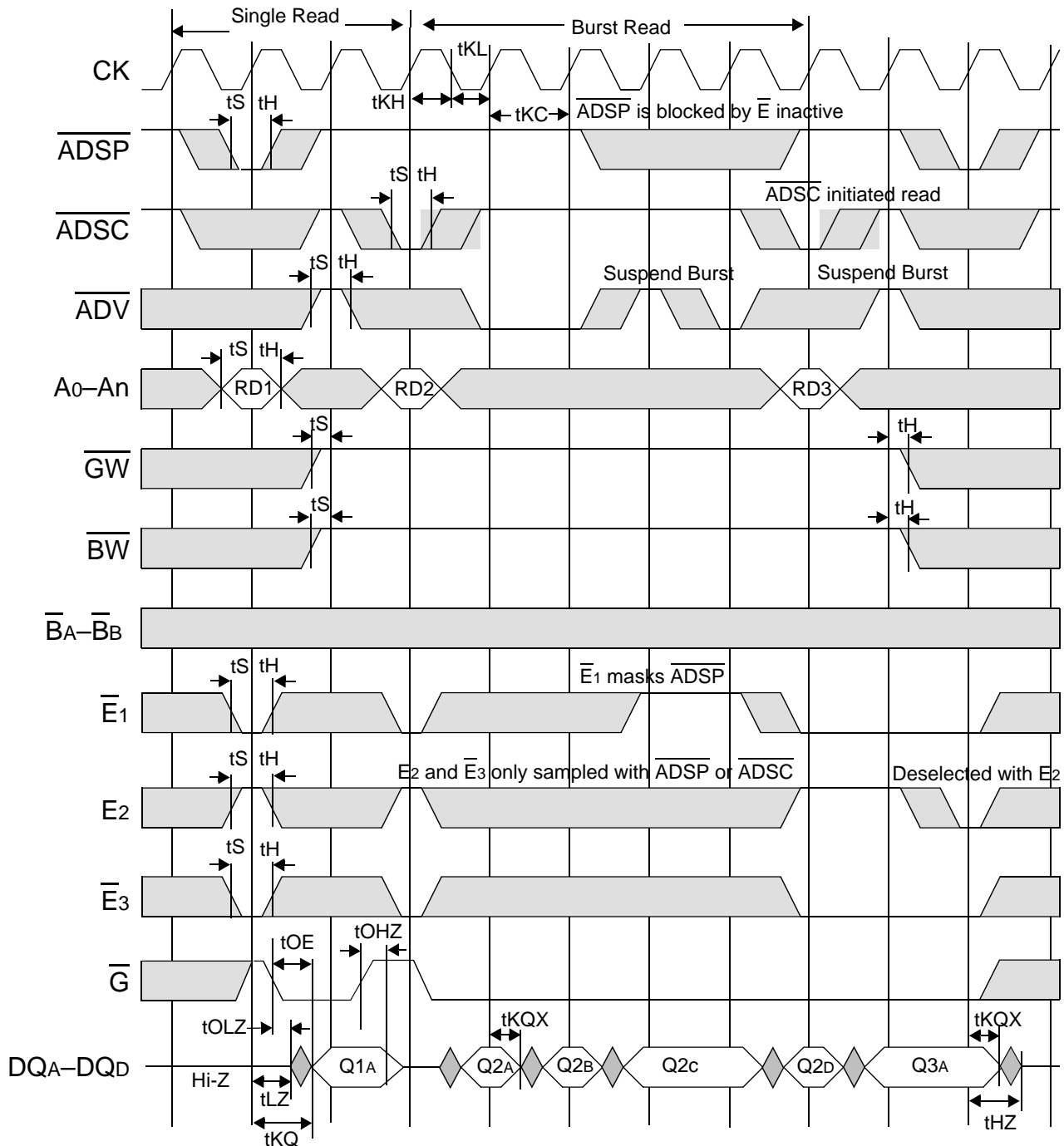
1. These parameters are sampled and are not 100% tested.
2. ZZ is an asynchronous signal. However, In order to be recognized on any given clock cycle, ZZ must meet the specified setup and hold times as specified above.

## Write Cycle Timing

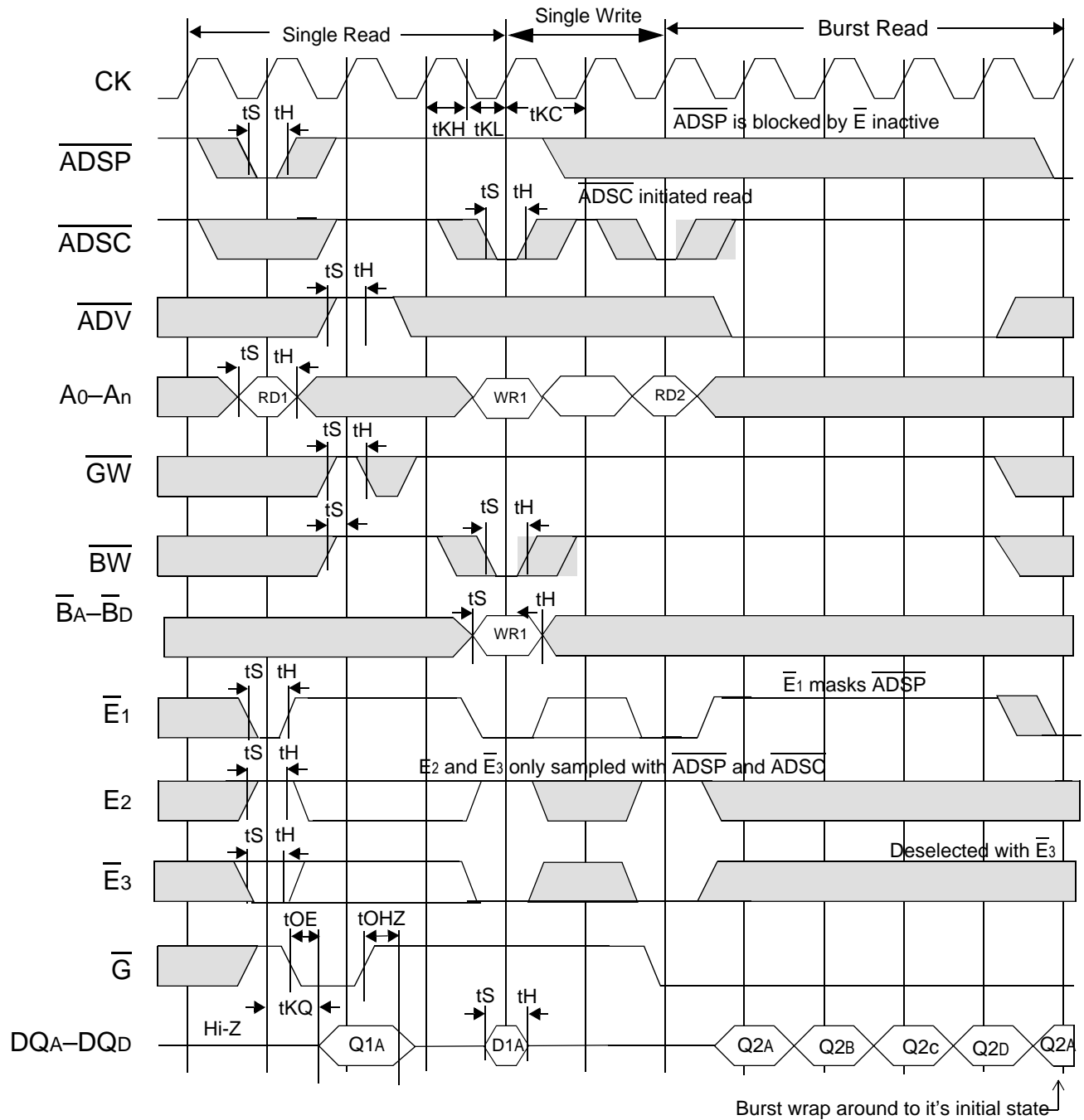




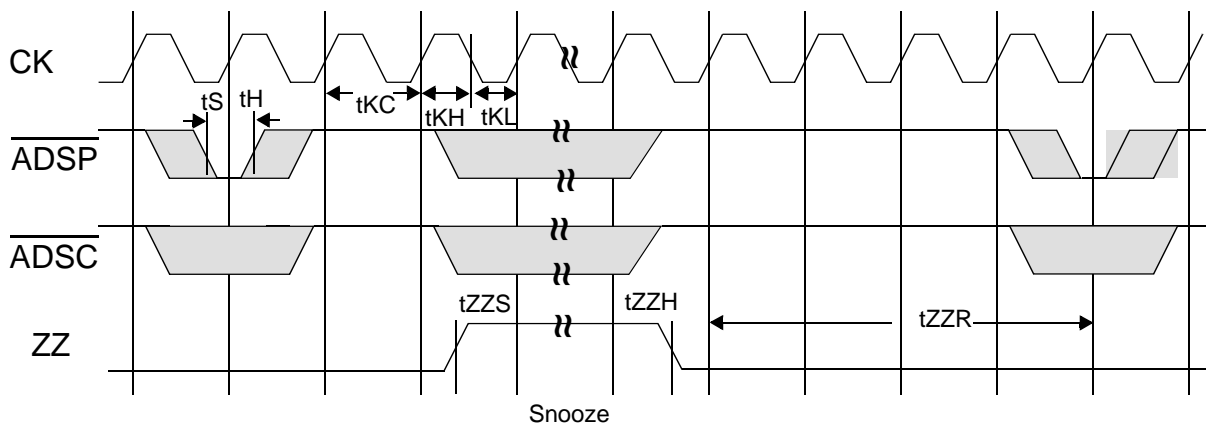
### Flow Through Read Cycle Timing



### Flow Through Read-Write Cycle Timing

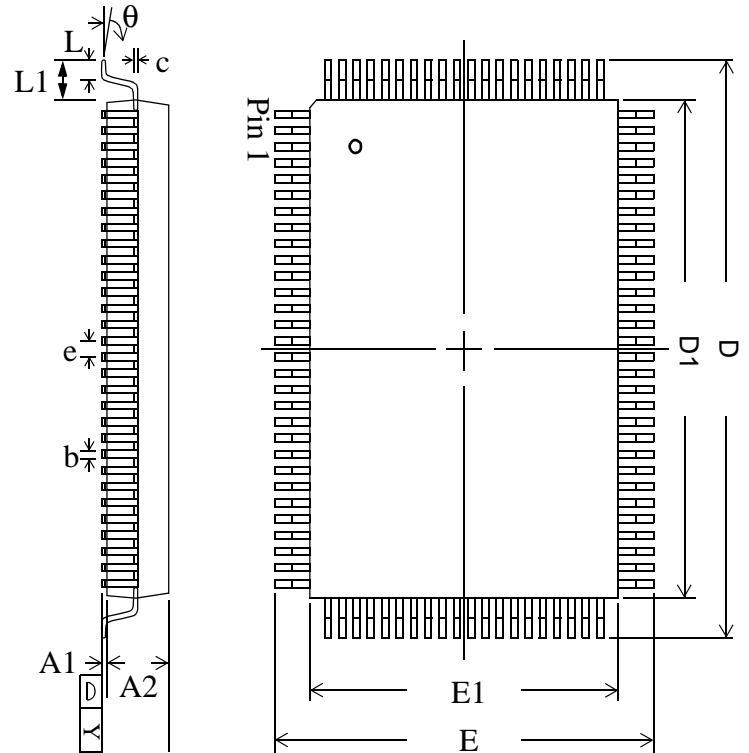


### Sleep Mode Timing Diagram



### TQFP Package Drawing

Symbol	Description	Min.	Nom.	Max
A1	Standoff	0.05	0.10	0.15
A2	Body Thickness	1.35	1.40	1.45
b	Lead Width	0.20	0.30	0.40
c	Lead Thickness	0.09	—	0.20
D	Terminal Dimension	21.9	22.0	22.1
D1	Package Body	19.9	20.0	20.1
E	Terminal Dimension	15.9	16.0	16.1
E1	Package Body	13.9	14.0	14.1
e	Lead Pitch	—	0.65	—
L	Foot Length	0.45	0.60	0.75
L1	Lead Length	—	1.00	—
Y	Coplanarity	—	—	0.10
$\theta$	Lead Angle	0°	—	7°



**Notes:**

1. All dimensions are in millimeters (mm).
2. Package width and length do not include mold protrusion.

### Ordering Information for GSI Synchronous Burst RAMs

Org	Part Number <sup>1</sup>	Type	Package	Speed <sup>2</sup> (MHz/ns)	T <sub>A</sub> <sup>3</sup>	Status
1M x 18	GS8150F18T-7	Flow Through	TQFP	7	C	
1M x 18	GS8150F18T-7.5	Flow Through	TQFP	7.5	C	
1M x 18	GS8150F18T-8	Flow Through	TQFP	8	C	
1M x 18	GS8150F18T-8.5	Flow Through	TQFP	8.5	C	
1M x 18	GS8150F18T-10	Flow Through	TQFP	10	C	
1M x 18	GS8150F18T-11	Flow Through	TQFP	11	C	
512K x 32	GS8150F36T-7	Flow Through	TQFP	7	C	
512K x 32	GS8150F36T-7.5	Flow Through	TQFP	7.5	C	
512K x 32	GS8150F36T-8	Flow Through	TQFP	8	C	
512K x 32	GS8150F36T-8.5	Flow Through	TQFP	8.5	C	
512K x 32	GS8150F36T-10	Flow Through	TQFP	10	C	
512K x 32	GS8150F36T-11	Flow Through	TQFP	11	C	
512K x 36	GS8150F36T-7	Flow Through	TQFP	7	C	
512K x 36	GS8150F36T-7.5	Flow Through	TQFP	7.5	C	
512K x 36	GS8150F36T-8	Flow Through	TQFP	8	C	
512K x 36	GS8150F36T-8.5	Flow Through	TQFP	8.5	C	
512K x 36	GS8150F36T-10	Flow Through	TQFP	10	C	
512K x 36	GS8150F36T-11	Flow Through	TQFP	11	C	
1M x 18	GS8150F18T-7I	Flow Through	TQFP	7	I	Not Available
1M x 18	GS8150F18T-7.5I	Flow Through	TQFP	7.5	I	Not Available
1M x 18	GS8150F18T-8I	Flow Through	TQFP	8	I	
1M x 18	GS8150F18T-8.5I	Flow Through	TQFP	8.5	I	
1M x 18	GS8150F18T-10I	Flow Through	TQFP	10	I	
1M x 18	GS8150F18T-11I	Flow Through	TQFP	11	I	
512K x 32	GS8150F36T-7I	Flow Through	TQFP	7	I	Not Available
512K x 32	GS8150F36T-7.5I	Flow Through	TQFP	7.5	I	Not Available
512K x 32	GS8150F36T-8I	Flow Through	TQFP	8	I	
512K x 32	GS8150F36T-8.5I	Flow Through	TQFP	8.5	I	
512K x 32	GS8150F36T-10I	Flow Through	TQFP	10	I	
512K x 32	GS8150F36T-11I	Flow Through	TQFP	11	I	

Notes:

- Customers requiring delivery in Tape and Reel should add the character T to the end of the part number. Example: GS8150F18-8T.
- The speed column indicates the cycle frequency (MHz) of the device in Pipeline mode and the latency (ns) in Flow Through mode. Each device is Pipeline/Flow through mode-selectable by the user.
- T<sub>A</sub> = C = Commercial Temperature Range. T<sub>A</sub> = I = Industrial Temperature Range.
- GSI offers other versions this type of device in many different configurations and with a variety of different features, only some of which are covered in this data sheet. See the GSI Technology web site ([www.gsistechnology.com](http://www.gsistechnology.com)) for a complete listing of current offerings.

Org	Part Number <sup>1</sup>	Type	Package	Speed <sup>2</sup> (MHz/ns)	T <sub>A</sub> <sup>3</sup>	Status
512K x 36	GS8150F36T-7I	Flow Through	TQFP	7	I	Not Available
512K x 36	GS8150F36T-7.5I	Flow Through	TQFP	7.5	I	Not Available
512K x 36	GS8150F36T-8I	Flow Through	TQFP	8	I	
512K x 36	GS8150F36T-8.5I	Flow Through	TQFP	8.5	I	
512K x 36	GS8150F36T-10I	Flow Through	TQFP	10	I	
512K x 36	GS8150F36T-11I	Flow Through	TQFP	11	I	

Notes:

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**0.18u 16M Sync SRAM Data Sheet Revision History**

<b>DS/DateRev. Code: Old; New</b>	<b>Types of Changes Format or Content</b>	<b>Page;Revisions;Reason</b>
8150F18_r1		• Creation of new datasheet
8150F18_r1; 8150F18_r1_01	Content	• Updated Features list on page 1 • Completely reworked table on page 1 • Updated Mode Pin Functions table on page 7